

L Number	Hits	Search Text	DB	Time stamp
1	36840	Lithography	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:31
2	224450	Lithography and semiconductor? or wafer? or chip?	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:32
3	24119	Semiconductor and lithography	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:32
4	3213	(Semiconductor and lithography) and (reticle or mask near2 chamber)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:33
6	1	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (chamber near2 opening)) and (opening near2 panel)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:34
7	2	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (opening near2 panel)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:49
8	3135	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (reticle or mask near2 stage)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:40
9	43	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (chamber near2 opening)) and (reticle or mask near2 stage)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:40
10	42	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (chamber near2 opening)) and (reticle or mask near2 stage)) and (remov\$5 near3 reticle or mask)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:42
11	1	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (chamber near2 opening)) and (reticle or mask near2 stage)) and (remov\$5 near3 reticle or mask)) and (angle? near2 opening)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:42
12	3	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (angle? near2 opening)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:46
13	2	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (angle? near2 chamber)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 09:46
5	51	((Semiconductor and lithography) and (reticle or mask near2 chamber)) and (chamber near2 opening)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:26
14	10251	((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:29
15	4	((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (opening near2 panel)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:33
16	1814	((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (reticle or mask near2 chamber)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:33
17	2006	((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (reticle or mask near2 stage)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:34
18	3582	((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (remov\$4 near3 reticle or mask)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:35

10/056,017

19	2	((((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (remov\$4 near3 reticle or mask)) and (angle? near2 chamber)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:37
20	7	((((250/492.2,492.22,492.21,492.3,396ML,) or (438/4,) or (257/678,) or (355/53,)).CCLS.) and (remov\$4 near3 reticle or mask)) and (angle? near2 stage)	USPAT; US-PGPUB; EPO; JPO	2003/08/19 10:37

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